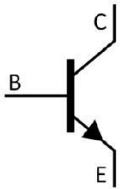


Silicon NPN transistor in a SOT-323 Plastic Package.

High voltage, complementary pair with MMBT5401W.

General purpose high voltage amplifier.



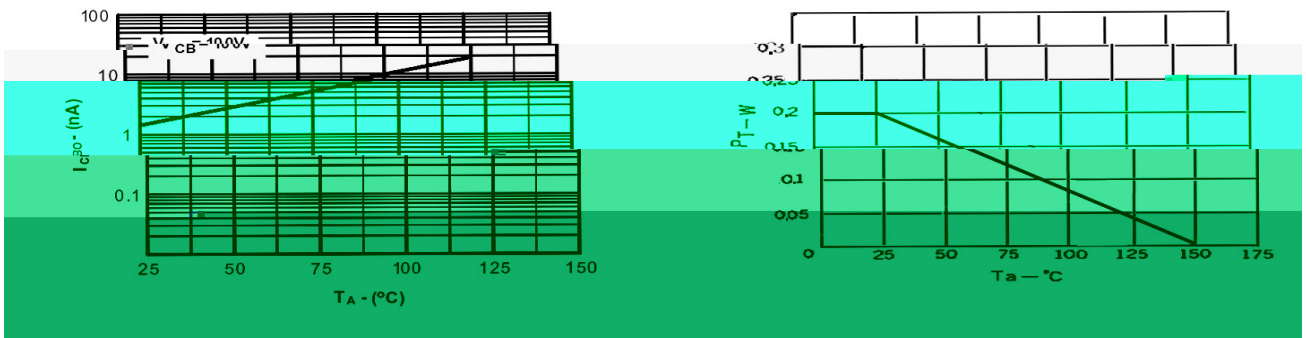
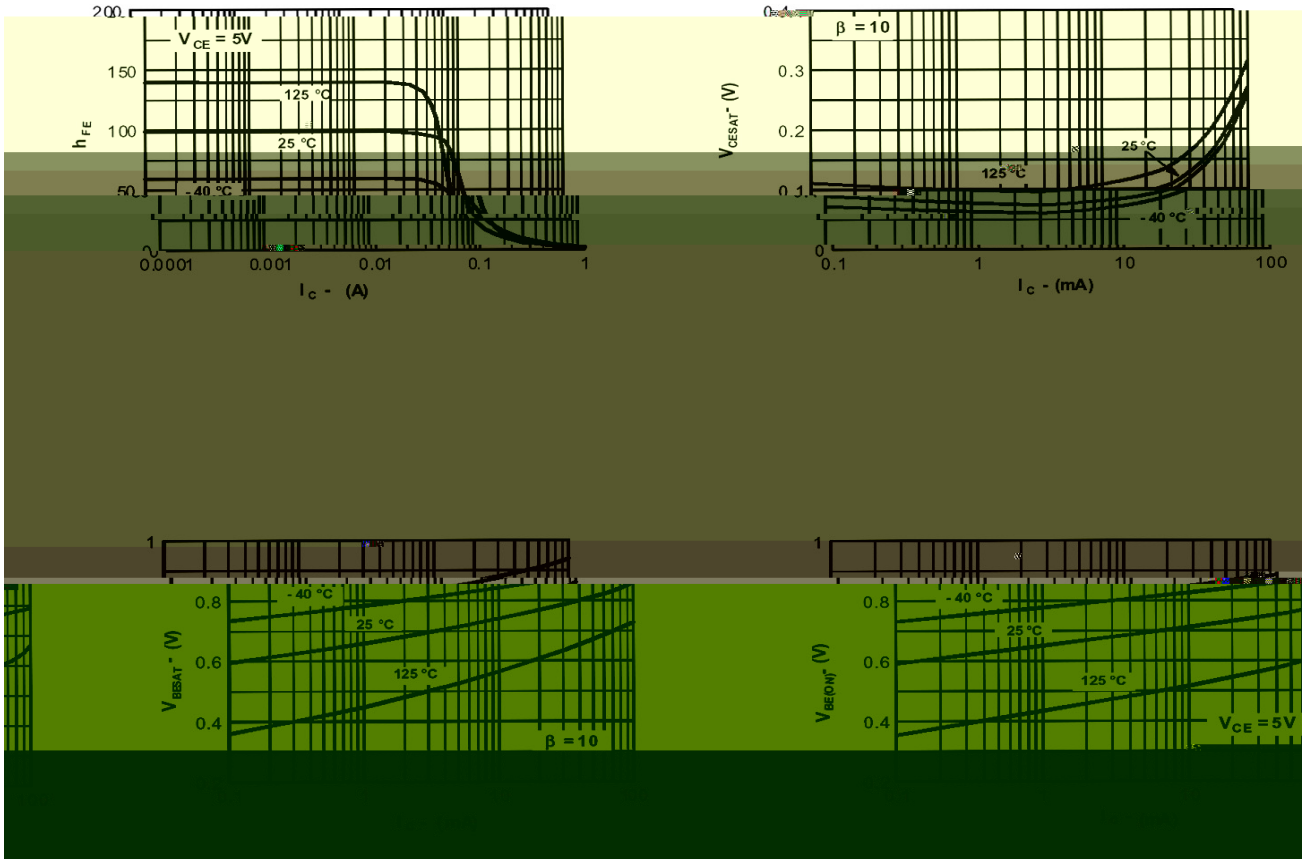
PIN1 Emitter PIN 2 Base PIN 3 Collector

h_{FE} Classifications Symbol	A	B	C
h_{FE} Range	50~150	100~300	200~400
Marking	HG1A	HG1B	HG1C

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA
Base Current - Continuous	I_B	300	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

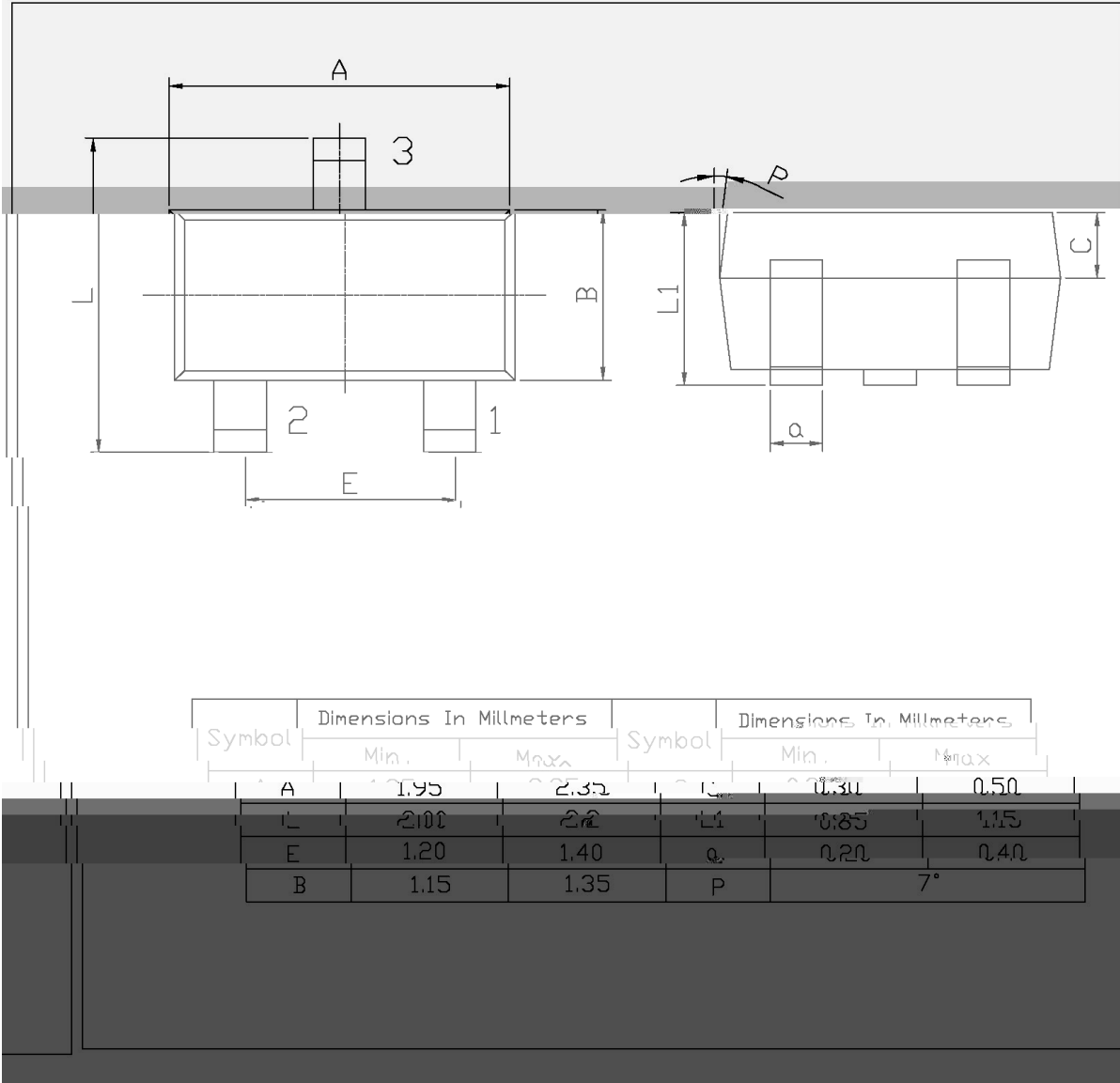
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=180V$ $I_E=0$			0.1	A
Emitter to Base Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			0.1	A
	$h_{FE(1)}$	$V_{CE}=5.0V$ I_C				

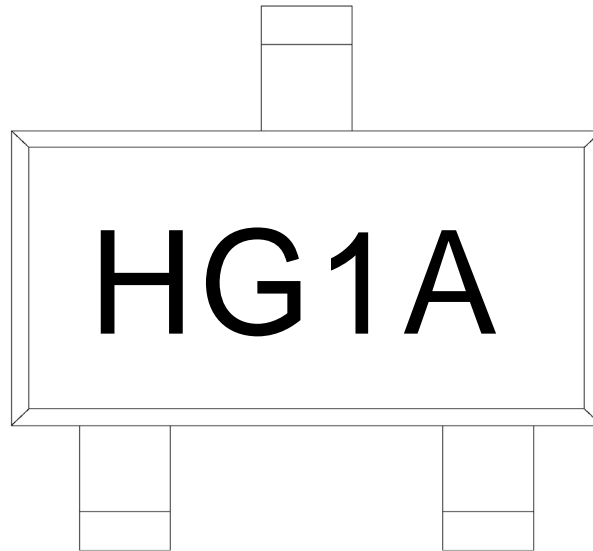
DC Current Gain



SOT-323

单位: mm





H

G1

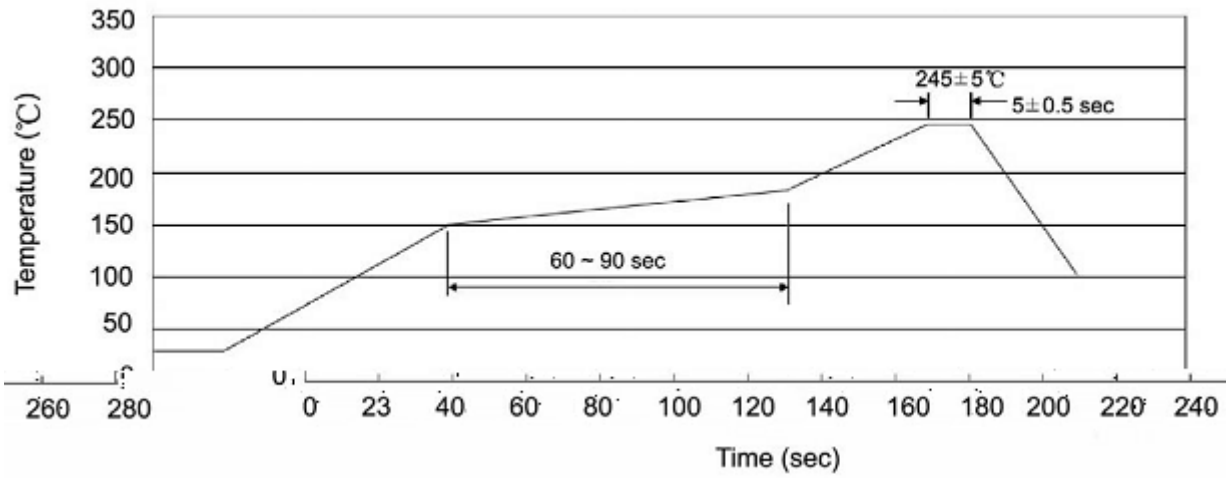
A h_{FE}

Note:

H: Company Code.

G1 Product Type.

A h_{FE} Classifications Symbol



Note:

- | | | | | | |
|---|-----|-----|----|---------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-323	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205